

# 74AUP1T97

Low-power configurable gate with voltage-level translator

Rev. 5 — 17 September 2015

Product data sheet

## 1. General description

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The 74AUP1T97 provides low-power, low-voltage configurable logic gate functions. The output state is determined by eight patterns of 3-bit input. The user can choose the logic functions MUX, AND, OR, NAND, NOR, inverter and buffer. All inputs can be connected to  $V_{CC}$  or GND.

This device ensures a very low static and dynamic power consumption across the entire  $V_{CC}$  range from 2.3 V to 3.6 V.

The 74AUP1T97 is designed for logic-level translation applications with input switching levels that accept 1.8 V low-voltage CMOS signals, while operating from either a single 2.5 V or 3.3 V supply voltage.

The wide supply voltage range ensures normal operation as battery voltage drops from 3.6 V to 2.3 V.

This device is fully specified for partial power-down applications using  $I_{OFF}$ . The  $I_{OFF}$  circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

Schmitt trigger inputs make the circuit tolerant to slower input rise and fall times across the entire  $V_{CC}$  range.

## 2. Features and benefits

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- Wide supply voltage range from 2.3 V to 3.6 V
- High noise immunity
- ESD protection:
  - ◆ HBM JESD22-A114F Class 3A exceeds 5000 V
  - ◆ MM JESD22-A115-A exceeds 200 V
  - ◆ CDM JESD22-C101E exceeds 1000 V
- Low static power consumption;  $I_{CC} = 1.5 \mu\text{A}$  (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of  $V_{CC}$
- $I_{OFF}$  circuitry provides partial power-down mode operation
- Multiple package options
- Specified from  $-40 \text{ }^\circ\text{C}$  to  $+85 \text{ }^\circ\text{C}$  and  $-40 \text{ }^\circ\text{C}$  to  $+125 \text{ }^\circ\text{C}$



### 3. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74AUP1T97GW	-40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363
74AUP1T97GM	-40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1.45 × 0.5 mm	SOT886
74AUP1T97GF	-40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1 × 0.5 mm	SOT891
74AUP1T97GN	-40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 0.9 × 1.0 × 0.35 mm	SOT1115
74AUP1T97GS	-40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 1.0 × 1.0 × 0.35 mm	SOT1202
74AUP1T97GX	-40 °C to +125 °C	X2SON6	plastic thermal extremely thin small outline package; no leads; 6 terminals; body 1 × 0.8 × 0.35 mm	SOT1255

### 4. Marking

Table 2. Marking

Type number	Marking code <sup>[1]</sup>
74AUP1T97GW	59
74AUP1T97GM	59
74AUP1T97GF	59
74AUP1T97GN	59
74AUP1T97GS	59
74AUP1T97GX	59

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

### 5. Functional diagram

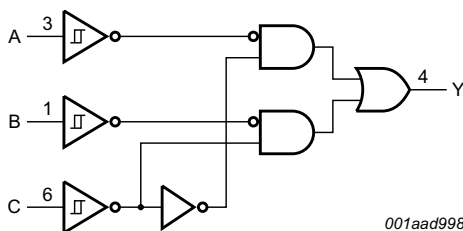


Fig 1. Logic symbol

## 6. Pinning information

### 6.1 Pinning

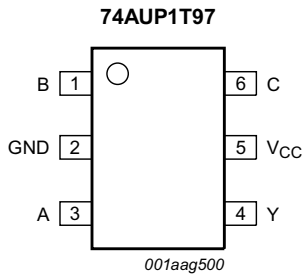


Fig 2. Pin configuration SOT363

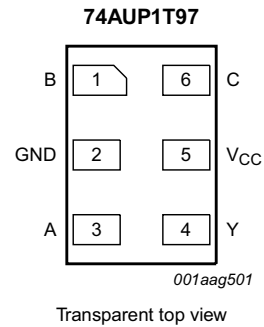


Fig 3. Pin configuration SOT886

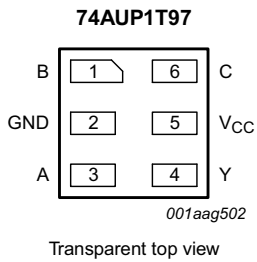


Fig 4. Pin configuration SOT891, SOT1115 and SOT1202

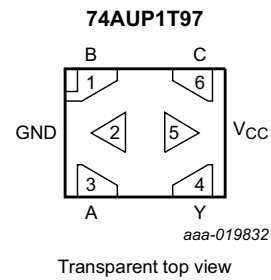


Fig 5. Pin configuration SOT1255 (X2SON6)

### 6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
B	1	data input
GND	2	ground (0 V)
A	3	data input
Y	4	data output
V <sub>CC</sub>	5	supply voltage
C	6	data input

## 7. Functional description

Table 4. Function table<sup>[1]</sup>

Input			Output
C	B	A	Y
L	L	L	L
L	L	H	L
L	H	L	H
L	H	H	H
H	L	L	L
H	L	H	H
H	H	L	L
H	H	H	H

[1] H = HIGH voltage level; L = LOW voltage level.

### 7.1 Logic configurations

Table 5. Function selection table

Logic function	Figure
2-input MUX	see <a href="#">Figure 6</a>
2-input AND	see <a href="#">Figure 7</a>
2-input OR with one input inverted	see <a href="#">Figure 8</a>
2-input NAND with one input inverted	see <a href="#">Figure 8</a>
2-input AND with one input inverted	see <a href="#">Figure 9</a>
2-input NOR with one input inverted	see <a href="#">Figure 9</a>
2-input OR	see <a href="#">Figure 10</a>
Inverter	see <a href="#">Figure 11</a>
Buffer	see <a href="#">Figure 12</a>

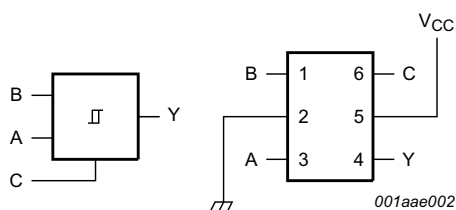


Fig 6. 2-input MUX

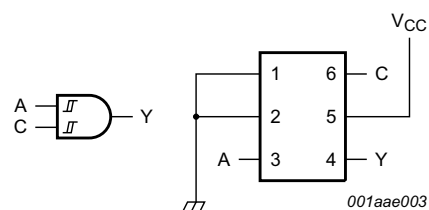
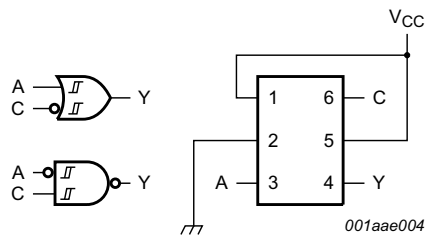
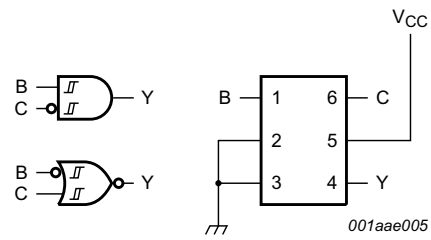


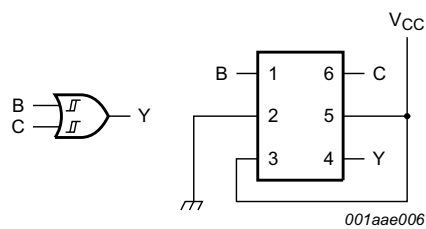
Fig 7. 2-input AND gate



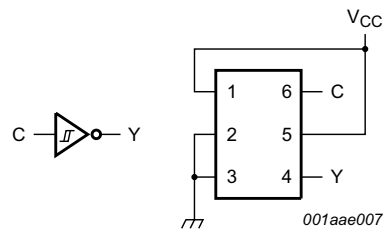
**Fig 8.** 2-input NAND gate with input A inverted or 2-input OR gate with input C inverted



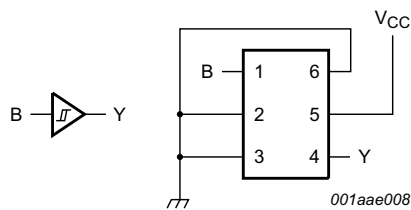
**Fig 9.** 2-input NOR gate with input B inverted or 2-input AND gate with input C inverted



**Fig 10.** 2-input OR gate



**Fig 11.** Inverter



**Fig 12.** Buffer

## 8. Limiting values

**Table 6. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+4.6	V
$I_{IK}$	input clamping current	$V_I < 0$ V	-50	-	mA
$V_I$	input voltage		-0.5	+4.6	V
$I_{OK}$	output clamping current	$V_O < 0$ V	-50	-	mA
$V_O$	output voltage	Active mode and Power-down mode	-0.5	+4.6	V
$I_O$	output current	$V_O = 0$ V to $V_{CC}$	-	$\pm 20$	mA
$I_{CC}$	supply current		-	50	mA
$I_{GND}$	ground current		-50	-	mA
$T_{stg}$	storage temperature		-65	+150	°C
$P_{tot}$	total power dissipation	$T_{amb} = -40$ °C to $+125$ °C	-	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SC-88 package: above 87.5 °C the value of  $P_{tot}$  derates linearly with 4.0 mW/K.

For X2SON6 and XSON6 packages: above 118 °C the value of  $P_{tot}$  derates linearly with 7.8 mW/K.

## 9. Recommended operating conditions

**Table 7. Recommended operating conditions**

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		2.3	3.6	V
$V_I$	input voltage		0	3.6	V
$V_O$	output voltage	Active mode	0	$V_{CC}$	V
		Power-down mode; $V_{CC} = 0$ V	0	3.6	V
$T_{amb}$	ambient temperature		-40	+125	°C

## 10. Static characteristics

**Table 8. Static characteristics**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>T<sub>amb</sub> = 25 °C</b>						
V <sub>T+</sub>	positive-going threshold voltage	V <sub>CC</sub> = 2.3 V to 2.7 V	0.60	-	1.10	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	0.75	-	1.16	V
V <sub>T-</sub>	negative-going threshold voltage	V <sub>CC</sub> = 2.3 V to 2.7 V	0.35	-	0.60	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	0.50	-	0.85	V
V <sub>H</sub>	hysteresis voltage	(V <sub>H</sub> = V <sub>T+</sub> - V <sub>T-</sub> )				
		V <sub>CC</sub> = 2.3 V to 2.7 V	0.23	-	0.60	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	0.25	-	0.56	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>T+</sub> or V <sub>T-</sub>				
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 2.3 V to 3.6 V	V <sub>CC</sub> - 0.1	-	-	V
		I <sub>O</sub> = -2.3 mA; V <sub>CC</sub> = 2.3 V	2.05	-	-	V
		I <sub>O</sub> = -3.1 mA; V <sub>CC</sub> = 2.3 V	1.9	-	-	V
		I <sub>O</sub> = -2.7 mA; V <sub>CC</sub> = 3.0 V	2.72	-	-	V
		I <sub>O</sub> = -4.0 mA; V <sub>CC</sub> = 3.0 V	2.6	-	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>T+</sub> or V <sub>T-</sub>				
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 2.3 V to 3.6 V	-	-	0.10	V
		I <sub>O</sub> = 2.3 mA; V <sub>CC</sub> = 2.3 V	-	-	0.31	V
		I <sub>O</sub> = 3.1 mA; V <sub>CC</sub> = 2.3 V	-	-	0.44	V
		I <sub>O</sub> = 2.7 mA; V <sub>CC</sub> = 3.0 V	-	-	0.31	V
		I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 3.0 V	-	-	0.44	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = GND to 3.6 V; V <sub>CC</sub> = 0 V to 3.6 V	-	-	±0.1	μA
I <sub>OFF</sub>	power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V	-	-	±0.1	μA
ΔI <sub>OFF</sub>	additional power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V to 0.2 V	-	-	±0.2	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = GND or V <sub>CC</sub> ; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 2.3 V to 3.6 V	-	-	1.2	μA
C <sub>I</sub>	input capacitance	V <sub>CC</sub> = 0 V to 3.6 V; V <sub>I</sub> = GND or V <sub>CC</sub>	-	0.8	-	pF
C <sub>O</sub>	output capacitance	V <sub>O</sub> = GND; V <sub>CC</sub> = 0 V	-	1.7	-	pF
<b>T<sub>amb</sub> = -40 °C to +85 °C</b>						
V <sub>T+</sub>	positive-going threshold voltage	V <sub>CC</sub> = 2.3 V to 2.7 V	0.60	-	1.10	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	0.75	-	1.19	V
V <sub>T-</sub>	negative-going threshold voltage	V <sub>CC</sub> = 2.3 V to 2.7 V	0.35	-	0.60	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	0.50	-	0.85	V
V <sub>H</sub>	hysteresis voltage	(V <sub>H</sub> = V <sub>T+</sub> - V <sub>T-</sub> )				
		V <sub>CC</sub> = 2.3 V to 2.7 V	0.10	-	0.60	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	0.15	-	0.56	V

**Table 8. Static characteristics ...continued**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>T+</sub> or V <sub>T-</sub>				
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 2.3 V to 3.6 V	V <sub>CC</sub> - 0.1	-	-	V
		I <sub>O</sub> = -2.3 mA; V <sub>CC</sub> = 2.3 V	1.97	-	-	V
		I <sub>O</sub> = -3.1 mA; V <sub>CC</sub> = 2.3 V	1.85	-	-	V
		I <sub>O</sub> = -2.7 mA; V <sub>CC</sub> = 3.0 V	2.67	-	-	V
		I <sub>O</sub> = -4.0 mA; V <sub>CC</sub> = 3.0 V	2.55	-	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>T+</sub> or V <sub>T-</sub>				
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 2.3 V to 3.6 V	-	-	0.1	V
		I <sub>O</sub> = 2.3 mA; V <sub>CC</sub> = 2.3 V	-	-	0.33	V
		I <sub>O</sub> = 3.1 mA; V <sub>CC</sub> = 2.3 V	-	-	0.45	V
		I <sub>O</sub> = 2.7 mA; V <sub>CC</sub> = 3.0 V	-	-	0.33	V
		I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 3.0 V	-	-	0.45	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = GND to 3.6 V; V <sub>CC</sub> = 0 V to 3.6 V	-	-	±0.5	μA
I <sub>OFF</sub>	power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V	-	-	±0.5	μA
ΔI <sub>OFF</sub>	additional power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V to 0.2 V	-	-	±0.5	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = GND or V <sub>CC</sub> ; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 2.3 V to 3.6 V	-	-	1.5	μA
ΔI <sub>CC</sub>	additional supply current	V <sub>CC</sub> = 2.3 V to 2.7 V; I <sub>O</sub> = 0 A <a href="#">[1]</a>	-	-	4	μA
		V <sub>CC</sub> = 3.0 V to 3.6 V; I <sub>O</sub> = 0 A <a href="#">[2]</a>	-	-	12	μA
<b>T<sub>amb</sub> = -40 °C to +125 °C</b>						
V <sub>T+</sub>	positive-going threshold voltage	V <sub>CC</sub> = 2.3 V to 2.7 V	0.60	-	1.10	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	0.75	-	1.19	V
V <sub>T-</sub>	negative-going threshold voltage	V <sub>CC</sub> = 2.3 V to 2.7 V	0.33	-	0.64	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	0.46	-	0.85	V
V <sub>H</sub>	hysteresis voltage	(V <sub>H</sub> = V <sub>T+</sub> - V <sub>T-</sub> )				
		V <sub>CC</sub> = 2.3 V to 2.7 V	0.10	-	0.60	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	0.15	-	0.56	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>T+</sub> or V <sub>T-</sub>				
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 2.3 V to 3.6 V	V <sub>CC</sub> - 0.11	-	-	V
		I <sub>O</sub> = -2.3 mA; V <sub>CC</sub> = 2.3 V	1.77	-	-	V
		I <sub>O</sub> = -3.1 mA; V <sub>CC</sub> = 2.3 V	1.67	-	-	V
		I <sub>O</sub> = -2.7 mA; V <sub>CC</sub> = 3.0 V	2.40	-	-	V
		I <sub>O</sub> = -4.0 mA; V <sub>CC</sub> = 3.0 V	2.30	-	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>T+</sub> or V <sub>T-</sub>				
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 2.3 V to 3.6 V	-	-	0.11	V
		I <sub>O</sub> = 2.3 mA; V <sub>CC</sub> = 2.3 V	-	-	0.36	V
		I <sub>O</sub> = 3.1 mA; V <sub>CC</sub> = 2.3 V	-	-	0.50	V
		I <sub>O</sub> = 2.7 mA; V <sub>CC</sub> = 3.0 V	-	-	0.36	V
		I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 3.0 V	-	-	0.50	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = GND to 3.6 V; V <sub>CC</sub> = 0 V to 3.6 V	-	-	±0.75	μA



**Table 8. Static characteristics ...continued**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{OFF}$	power-off leakage current	$V_I$ or $V_O = 0\text{ V to }3.6\text{ V}$ ; $V_{CC} = 0\text{ V}$	-	-	$\pm 0.75$	$\mu\text{A}$
$\Delta I_{OFF}$	additional power-off leakage current	$V_I$ or $V_O = 0\text{ V to }3.6\text{ V}$ ; $V_{CC} = 0\text{ V to }0.2\text{ V}$	-	-	$\pm 0.75$	$\mu\text{A}$
$I_{CC}$	supply current	$V_I = \text{GND or }V_{CC}$ ; $I_O = 0\text{ A}$ ; $V_{CC} = 2.3\text{ V to }3.6\text{ V}$	-	-	3.5	$\mu\text{A}$
$\Delta I_{CC}$	additional supply current	$V_{CC} = 2.3\text{ V to }2.7\text{ V}$ ; $I_O = 0\text{ A}$ [1]	-	-	7	$\mu\text{A}$
		$V_{CC} = 3.0\text{ V to }3.6\text{ V}$ ; $I_O = 0\text{ A}$ [2]	-	-	22	$\mu\text{A}$

[1] One input at 0.3 V or 1.1 V, other input at  $V_{CC}$  or GND.

[2] One input at 0.45 V or 1.2 V, other input at  $V_{CC}$  or GND.

## 11. Dynamic characteristics

**Table 9. Dynamic characteristics**

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 14.

Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C			Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max (85 °C)	Max (125 °C)	
<b><math>V_{CC} = 2.3\text{ V to }2.7\text{ V}</math>; <math>V_I = 1.65\text{ V to }1.95\text{ V}</math></b>									
$t_{pd}$	propagation delay	A, B, C to Y; see Figure 13 [2]							
		$C_L = 5\text{ pF}$	2.2	3.5	5.5	0.5	6.8	7.5	ns
		$C_L = 10\text{ pF}$	2.6	4.1	6.3	1.0	7.9	8.7	ns
		$C_L = 15\text{ pF}$	2.9	4.6	6.9	1.0	8.7	9.6	ns
		$C_L = 30\text{ pF}$	3.7	5.8	8.4	1.5	10.8	11.9	ns
<b><math>V_{CC} = 2.3\text{ V to }2.7\text{ V}</math>; <math>V_I = 2.3\text{ V to }2.7\text{ V}</math></b>									
$t_{pd}$	propagation delay	A, B, C to Y; see Figure 13 [2]							
		$C_L = 5\text{ pF}$	1.8	3.4	5.5	0.5	6.0	6.6	ns
		$C_L = 10\text{ pF}$	2.2	4.0	6.2	1.0	7.1	7.9	ns
		$C_L = 15\text{ pF}$	2.5	4.4	6.8	1.0	7.9	8.7	ns
		$C_L = 30\text{ pF}$	3.2	5.6	8.3	1.5	10.0	11.0	ns
<b><math>V_{CC} = 2.3\text{ V to }2.7\text{ V}</math>; <math>V_I = 3.0\text{ V to }3.6\text{ V}</math></b>									
$t_{pd}$	propagation delay	A, B, C to Y; see Figure 13 [2]							
		$C_L = 5\text{ pF}$	1.4	3.1	5.0	0.5	5.5	6.1	ns
		$C_L = 10\text{ pF}$	1.8	3.7	5.7	1.0	6.5	7.2	ns
		$C_L = 15\text{ pF}$	2.2	4.2	6.3	1.0	7.4	8.2	ns
		$C_L = 30\text{ pF}$	2.9	5.3	7.9	1.5	9.5	10.5	ns
<b><math>V_{CC} = 3.0\text{ V to }3.6\text{ V}</math>; <math>V_I = 1.65\text{ V to }1.95\text{ V}</math></b>									
$t_{pd}$	propagation delay	A, B, C to Y; see Figure 13 [2]							
		$C_L = 5\text{ pF}$	2.1	2.9	3.9	0.5	8.0	8.8	ns
		$C_L = 10\text{ pF}$	2.5	3.4	4.6	1.0	8.5	9.4	ns
		$C_L = 15\text{ pF}$	2.9	3.9	5.2	1.0	9.1	10.1	ns
		$C_L = 30\text{ pF}$	3.6	5.0	6.7	1.5	9.8	10.8	ns

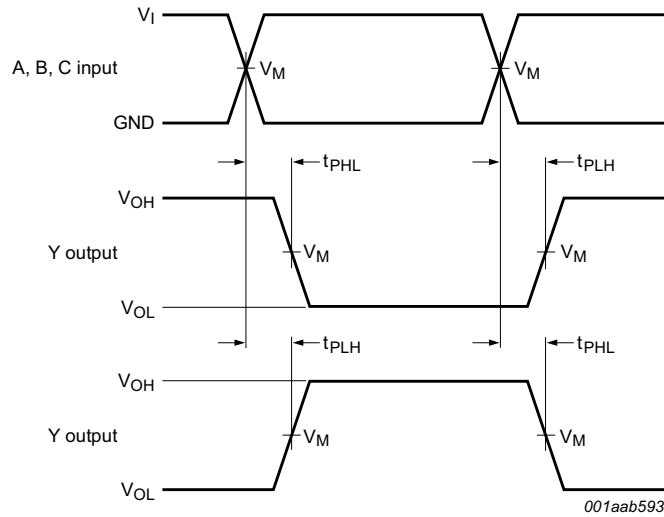
**Table 9. Dynamic characteristics ...continued**

*Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 14.*

Symbol	Parameter	Conditions	25 °C			–40 °C to +125 °C			Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max (85 °C)	Max (125 °C)	
<b>V<sub>CC</sub> = 3.0 V to 3.6 V; V<sub>I</sub> = 2.3 V to 2.7 V</b>									
t <sub>pd</sub>	propagation delay	A, B, C to Y; see Figure 13 [2]							
		C <sub>L</sub> = 5 pF	1.7	2.8	4.2	0.5	5.3	5.9	ns
		C <sub>L</sub> = 10 pF	2.1	3.4	5.0	1.0	6.1	6.8	ns
		C <sub>L</sub> = 15 pF	2.4	3.8	5.6	1.0	6.8	7.5	ns
		C <sub>L</sub> = 30 pF	3.2	5.0	7.1	1.5	8.5	9.4	ns
<b>V<sub>CC</sub> = 3.0 V to 3.6 V; V<sub>I</sub> = 3.0 V to 3.6 V</b>									
t <sub>pd</sub>	propagation delay	A, B, C to Y; see Figure 13 [2]							
		C <sub>L</sub> = 5 pF	1.4	2.7	4.2	0.5	4.7	5.2	ns
		C <sub>L</sub> = 10 pF	1.8	3.3	5.0	1.0	5.7	6.3	ns
		C <sub>L</sub> = 15 pF	2.1	3.8	5.6	1.0	6.2	6.9	ns
		C <sub>L</sub> = 30 pF	2.9	4.9	7.1	1.5	7.8	8.6	ns
<b>T<sub>amb</sub> = 25 °C</b>									
C <sub>PD</sub>	power dissipation capacitance	f <sub>i</sub> = 1 MHz; V <sub>I</sub> = GND to V <sub>CC</sub> [3]							
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	3.6	-	-	-	-	pF
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	4.3	-	-	-	-	pF

- [1] All typical values are measured at nominal V<sub>CC</sub>.
- [2] t<sub>pd</sub> is the same as t<sub>PLH</sub> and t<sub>PHL</sub>
- [3] C<sub>PD</sub> is used to determine the dynamic power dissipation (P<sub>D</sub> in μW).  
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$  where:  
 f<sub>i</sub> = input frequency in MHz;  
 f<sub>o</sub> = output frequency in MHz;  
 C<sub>L</sub> = output load capacitance in pF;  
 V<sub>CC</sub> = supply voltage in V;  
 N = number of inputs switching;  
 Σ(C<sub>L</sub> × V<sub>CC</sub><sup>2</sup> × f<sub>o</sub>) = sum of the outputs.

12. Waveforms



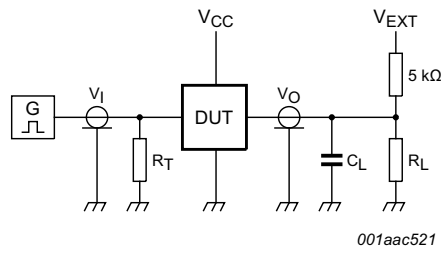
Measurement points are given in [Table 10](#).

$V_{OL}$  and  $V_{OH}$  are typical output voltage drop that occur with the output load.

Fig 13. Input A, B and C to output Y propagation delay times.

Table 10. Measurement points

Supply voltage	Output	Input		$t_r = t_f$
$V_{CC}$	$V_M$	$V_M$	$V_I$	
2.3 V to 3.6 V	$0.5V_{CC}$	$0.5V_I$	1.65 V to 3.6 V	$\leq 3.0$ ns



Test data is given in [Table 11](#).

Definitions for test circuit:

$R_L$  = Load resistance.

$C_L$  = Load capacitance including jig and probe capacitance.

$R_T$  = Termination resistance should be equal to the output impedance  $Z_o$  of the pulse generator.

$V_{EXT}$  = External voltage for measuring switching times.

**Fig 14. Test circuit for measuring switching times**

**Table 11. Test data**

Supply voltage	Load		$V_{EXT}$		
$V_{CC}$	$C_L$	$R_L$ [1]	$t_{PLH}$ , $t_{PHL}$	$t_{PZH}$ , $t_{PHZ}$	$t_{PZL}$ , $t_{PLZ}$
2.3 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 kΩ or 1 MΩ	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times  $R_L = 5\text{ k}\Omega$ , for measuring propagation delays, setup and hold times and pulse width  $R_L = 1\text{ M}\Omega$ .

13. Package outline

Plastic surface-mounted package; 6 leads

SOT363

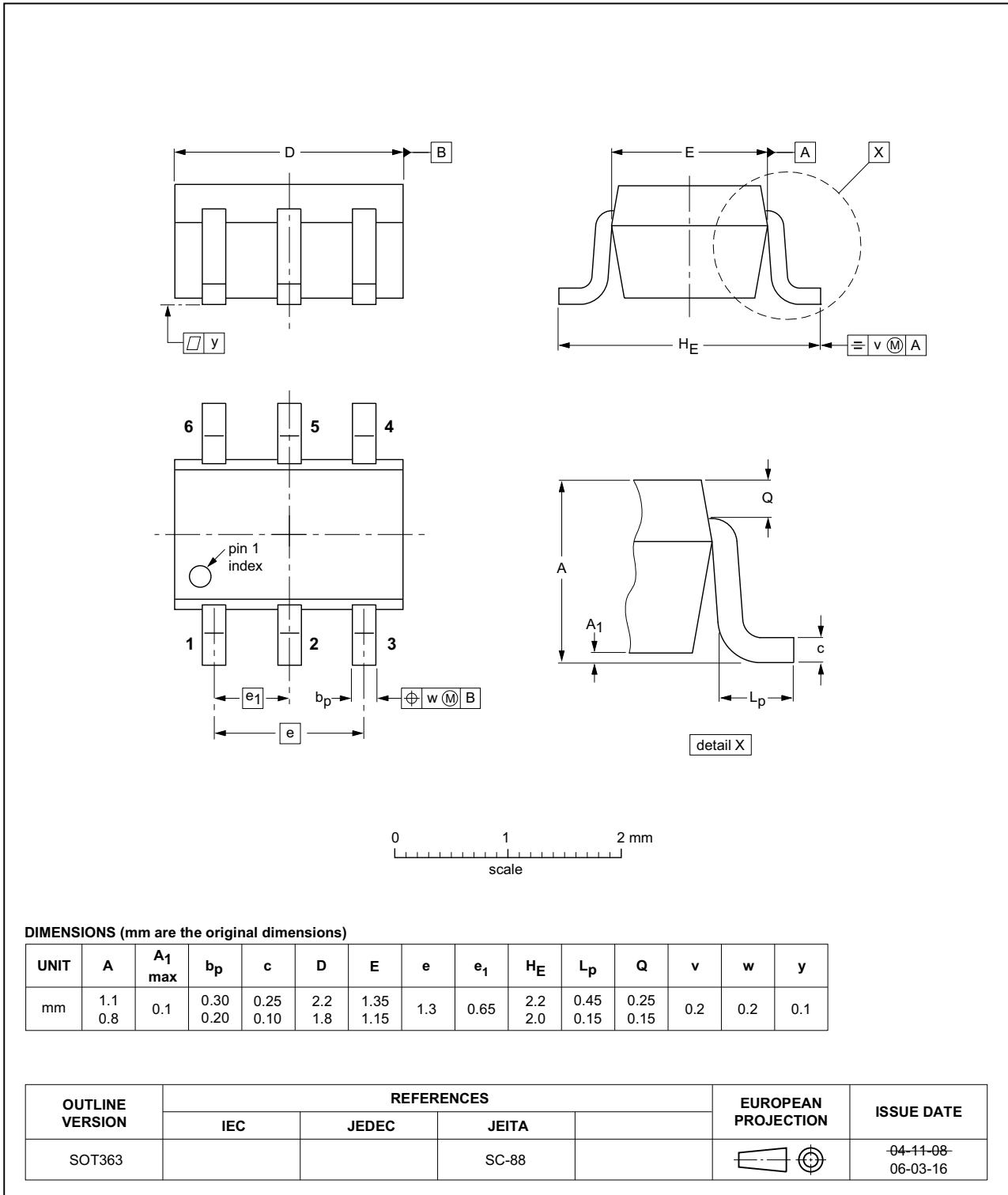


Fig 15. Package outline SOT363 (SC-88)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm

SOT886

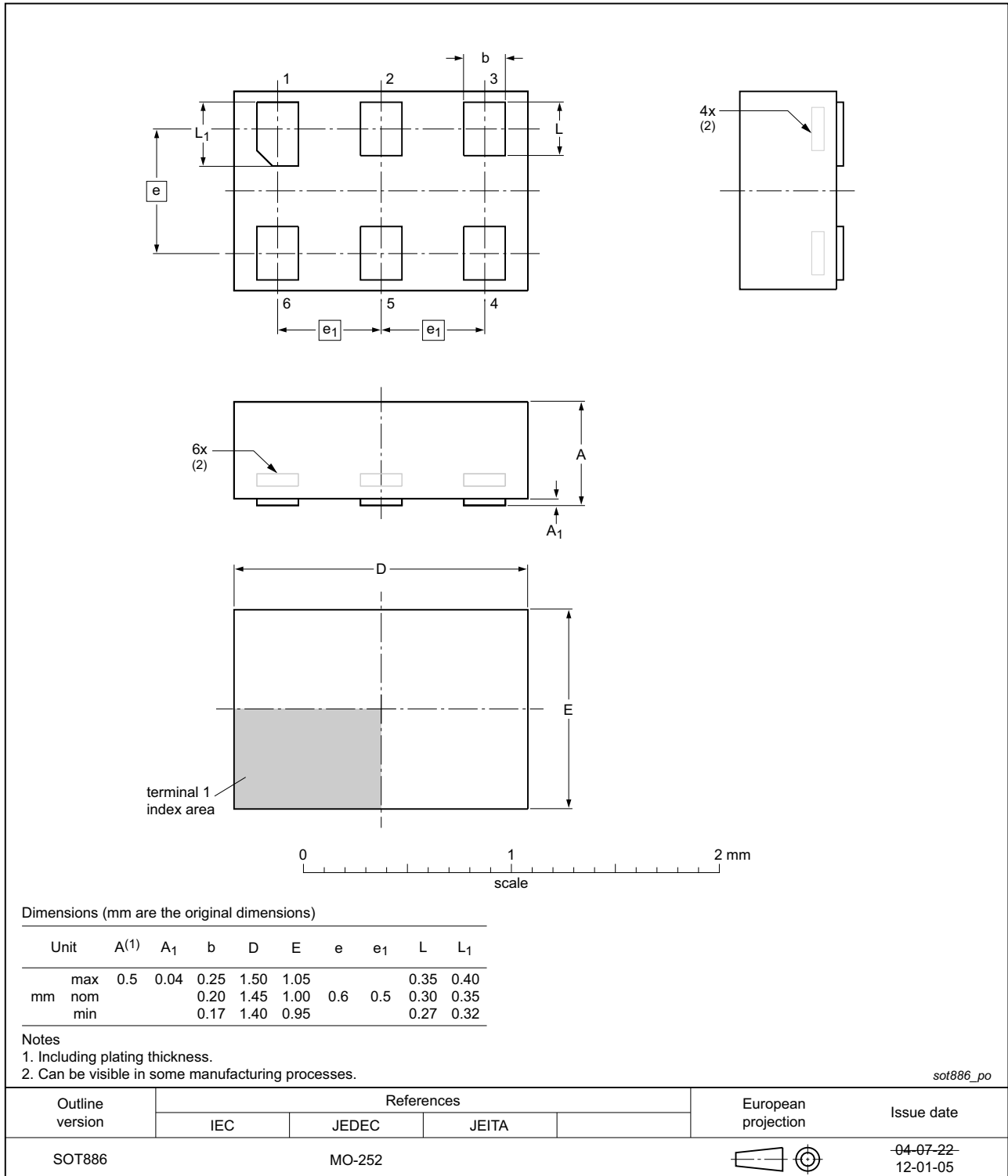


Fig 16. Package outline SOT886 (XSON6)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1 x 0.5 mm

SOT891

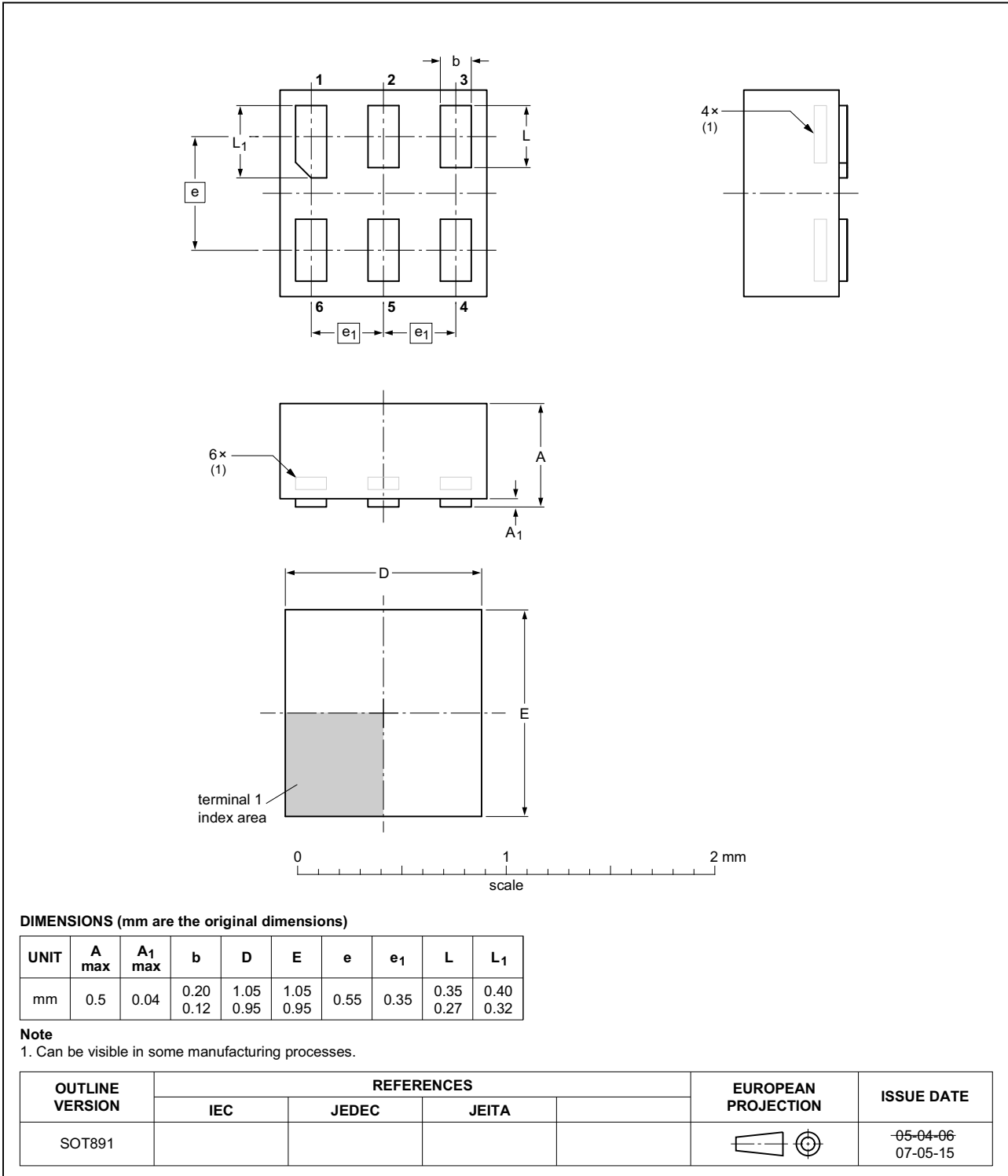


Fig 17. Package outline SOT891 (XSON6)

**XSON6: extremely thin small outline package; no leads;  
6 terminals; body 0.9 x 1.0 x 0.35 mm**

SOT1115

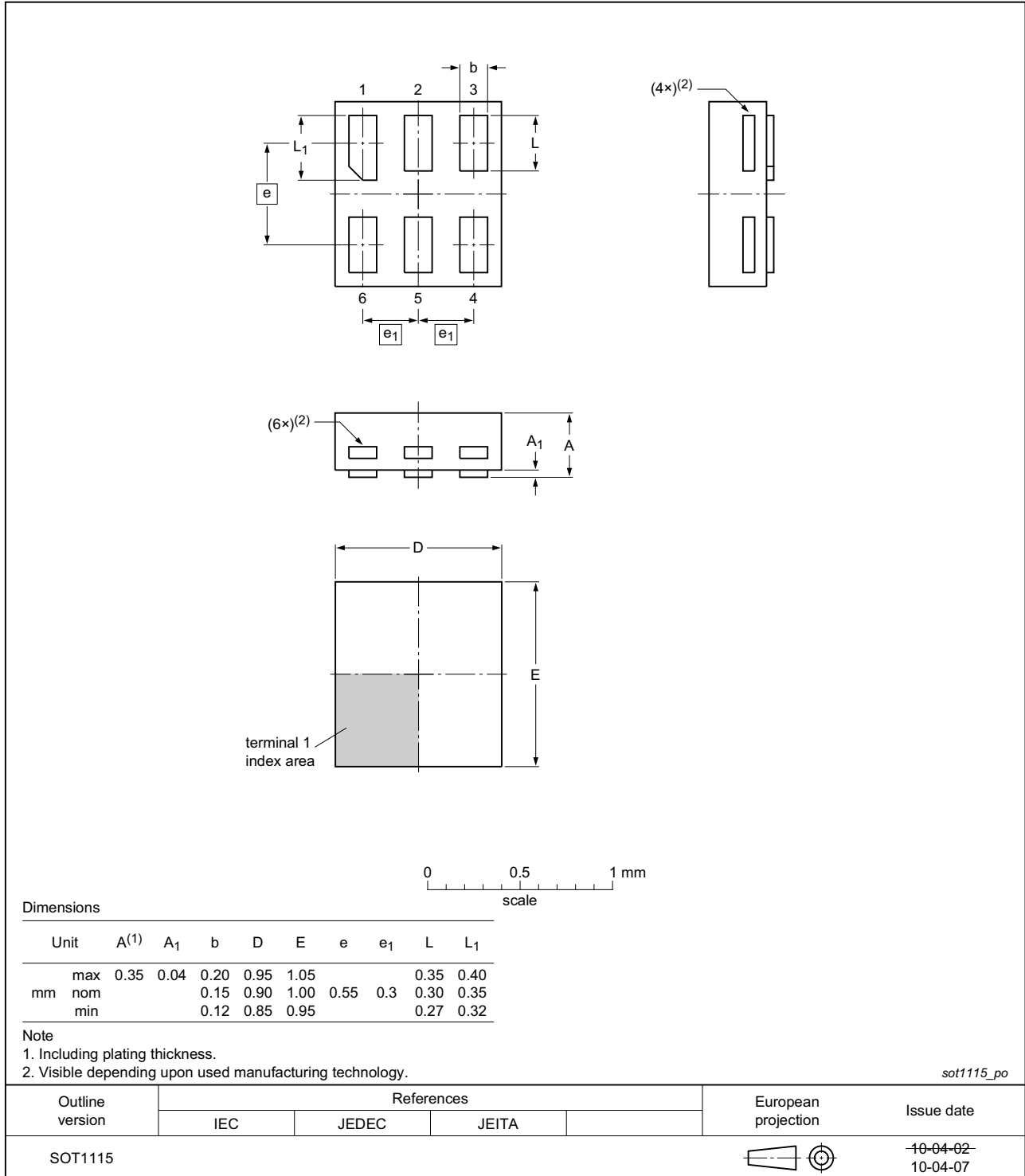
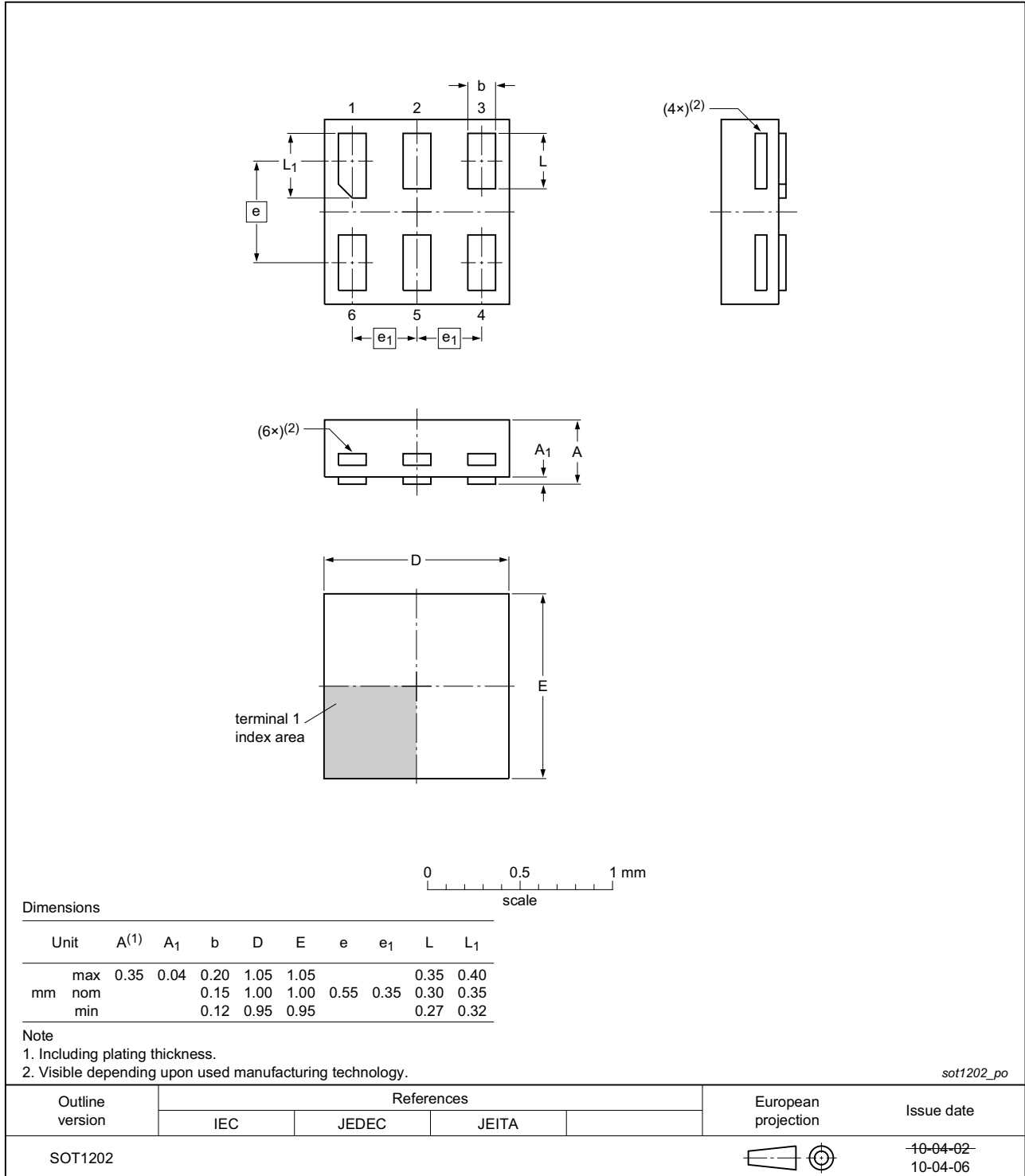


Fig 18. Package outline SOT1115 (XSON6)



**XSON6: extremely thin small outline package; no leads;  
6 terminals; body 1.0 x 1.0 x 0.35 mm**

**SOT1202**



**Fig 19. Package outline SOT1202 (XSON6)**

**X2SON6: plastic thermal enhanced extremely thin small outline package; no leads;  
6 terminals; body 1.0 x 0.8 x 0.35 mm**

SOT1255

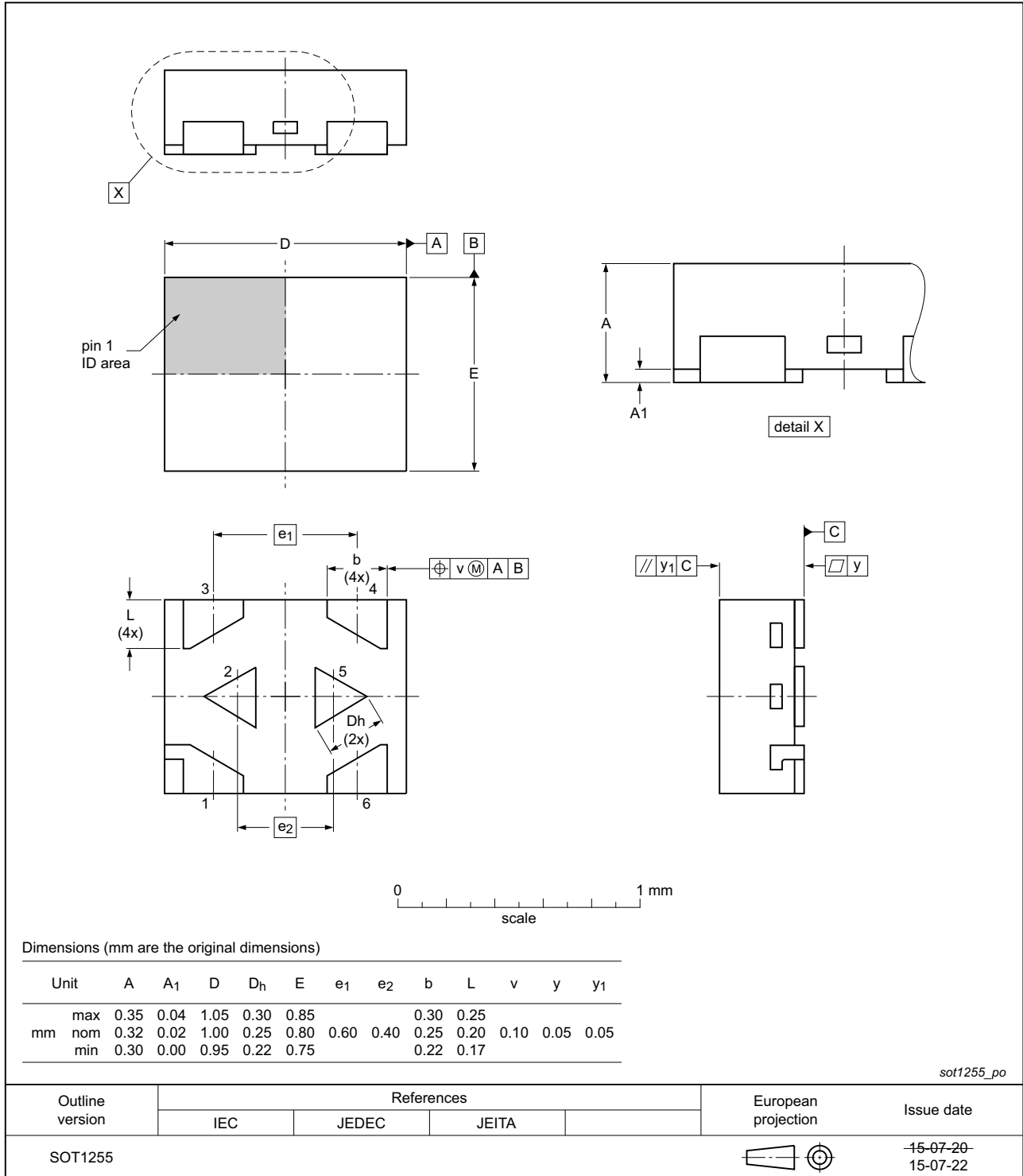


Fig 20. Package outline SOT1255 (X2SON6)

## 14. Abbreviations

Table 12. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

## 15. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1T97 v.5	20150917	Product data sheet	-	74AUP1T97 v.4
Modifications:	<ul style="list-style-type: none"> <li>Added type number 74AUP1T97GX (SOT1255/X2SON6).</li> </ul>			
74AUP1T97 v.4	20120815	Product data sheet	-	74AUP1T97 v.3
Modifications:	<ul style="list-style-type: none"> <li>Package outline drawing of SOT886 (<a href="#">Figure 16</a>) modified.</li> </ul>			
74AUP1T97 v.3	20111130	Product data sheet	-	74AUP1T97 v.2
74AUP1T97 v.2	20101018	Product data sheet	-	74AUP1T97 v.1
74AUP1T97 v.1	20071025	Product data sheet	-	-

## 16. Legal information

### 16.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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